

ABSTRACT OF THE DISCLOSURE

It is disclosed an over-coating agent for forming fine patterns which is applied to cover a substrate having thereon photoresist patterns and allowed to shrink under heat so that the spacing between adjacent photoresist patterns is lessened, with the applied film of the over-coating agent being removed substantially completely to form or define fine trace patterns, further characterized by containing a water-soluble polymer and a water-soluble fluorine compound (e.g. a fluoroalkyl alcohol or a fluoroalkyl carboxylic acid). Also disclosed is a method of forming fine-line patterns using the over-coating agent. According to the invention, one can reduce microfoaming and defects to produce fine-line patterns that have good leveling and coating properties and which also present satisfactory profiles and meet the characteristics required of today's semiconductor devices.